



FQD7N20L / FQU7N20L

200V LOGIC N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation modes. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, and motor control.

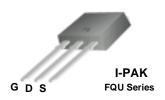
Features

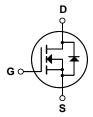
- 5.5A, 200V, $R_{DS(on)} = 0.75\Omega @V_{GS} = 10 V$
- Low gate charge (typical 6.8 nC)
- Low Crss (typical 8.5 pF)
- · Fast switching
- 100% avalanche tested
- · Improved dv/dt capability
- Low level gate drive requirement allowing direct operation from logic drivers

 PREBATION

 **PREBAT
- RoHS Compliant







Rev. A3, October 2008

Absolute Maximum Ratings $T_C = 25$ °C unless otherwise noted

| Symbol | Parameter | | FQD7N20L / FQU7N20L | Units |
|-------------------|--|----------|---------------------|-------|
| V _{DSS} | Drain-Source Voltage | | 200 | V |
| I _D | Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C) | | 5.5 | А |
| | | | 3.48 | А |
| I _{DM} | Drain Current - Pulsed | (Note 1) | 22 | Α |
| V _{GSS} | Gate-Source Voltage | | ± 20 | V |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 73 | mJ |
| I _{AR} | Avalanche Current (Note 1) | | 5.5 | А |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 4.5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 5.5 | V/ns |
| P _D | Power Dissipation (T _A = 25°C) * | | 2.5 | W |
| | Power Dissipation (T _C = 25°C) - Derate above 25°C | | 45 | W |
| | | | 0.36 | W/°C |
| T_J , T_{STG} | Operating and Storage Temperature Range | | -55 to +150 | °C |
| T _L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | Тур | Max | Units |
|-----------------|---|-----|------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | - | 2.78 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient * | | 50 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | | 110 | °C/W |

* When mounted on the minimum pad size recommended (PCB Mount)

| Symbol | Parameter | Test Conditions | i | Min | Тур | Max | Units |
|------------------------------------|---|--|----------|-----|------|------|----------|
| Off Cha | aracteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 200 | | | V |
| ΔBV_{DSS} / ΔT_{J} | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced | to 25°C | | 0.17 | | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 200 V, V _{GS} = 0 V | | | | 1 | μΑ |
| | | V _{DS} = 160 V, T _C = 125°C | | | | 10 | μΑ |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 20 V, V _{DS} = 0 V | | | | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -20 V, V _{DS} = 0 V | | | | -100 | nA |
| On Cha | racteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | 1.0 | | 2.0 | V |
| R _{DS(on)} | Static Drain-Source | $V_{GS} = 10 \text{ V}, I_D = 2.75 \text{ A}$ | | | 0.59 | 0.75 | - |
| - DS(0II) | On-Resistance | $V_{GS} = 5 \text{ V}, I_D = 2.75 \text{ A}$ | (Note 4) | | 0.62 | 0.78 | Ω |
| 9 _{FS} | Forward Transconductance | V _{DS} = 30 V, I _D = 2.75 A | | | 5.6 | | S |
| Dynam i | ic Characteristics Input Capacitance | | | | 390 | 500 | pF |
| | Output Capacitance | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz | | | 55 | 70 | • |
| C _{oss} | Reverse Transfer Capacitance | | | | 8.5 | 11 | pF pF |
| orss | Neverse Hansier Capacitance | | | | 0.0 | | рі |
| Switchi | ng Characteristics | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 100 \text{ V}, I_{D} = 6.5 \text{ A},$ $R_{G} = 25 \Omega$ | | | 12 | 35 | ns |
| t _r | Turn-On Rise Time | | | | 125 | 260 | ns |
| t _{d(off)} | Turn-Off Delay Time | (Note 4, 5) | | | 20 | 50 | ns |
| t _f | Turn-Off Fall Time | | | | 65 | 140 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 160 \text{ V}, I_{D} = 6.5 \text{ A},$ | | | 6.8 | 9.0 | nC |
| Q_{gs} | Gate-Source Charge | V _{GS} = 5 V (Note 4, 5) | | | 1.6 | | nC |
| Q_{gd} | Gate-Drain Charge | | | | 3.4 | | nC |
| Drain-S | ource Diode Characteristics a | nd Maximum Ratings | 5 | | | | |
| Is | Maximum Continuous Drain-Source Diode Forward Current | | | | 5.5 | Α | |
| I _{SM} | Maximum Pulsed Drain-Source Diode F | | | | | 22 | Α |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = 5.5 \text{ A}$ | | | | 1.5 | V |
| t _{rr} | Reverse Recovery Time | $V_{GS} = 0 \text{ V}, I_{S} = 6.5 \text{ A},$ | (Note 4) | | 110 | | ns |
| Q_{rr} | Reverse Recovery Charge | $dI_{F} / dt = 100 A/\mu s$ | | | 0.44 | | μC |

- $\label{eq:Notes:Notes:} \textbf{Notes:} \\ 1. \ \text{Repetitive Rating: Pulse width limited by maximum junction temperature} \\ 2. \ L = 3.6\text{mH}, \ I_{AS} = 5.5\text{A}, \ V_{DD} = 50\text{V}, \ R_G = 25\ \Omega, \ \text{Starting} \quad T_J = 25^{\circ}\text{C} \\ 3. \ I_{SD} \le 6.5\text{A}, \ \text{di/dt} \le 300\text{A/µs}, \ V_{DD} \le B\text{V}_{DS}, \ \text{Starting} \quad T_J = 25^{\circ}\text{C} \\ 4. \ \text{Pulse Test: Pulse width} \le 300\text{Qus}, \ \text{Duty cycle} \le 2\% \\ 5. \ \text{Essentially independent of operating temperature} \\ \end{aligned}$

Typical Characteristics

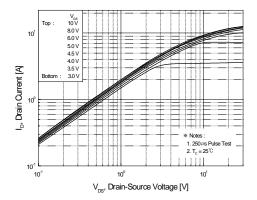


Figure 1. On-Region Characteristics

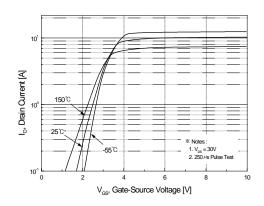


Figure 2. Transfer Characteristics

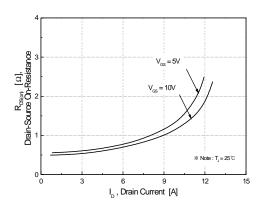


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

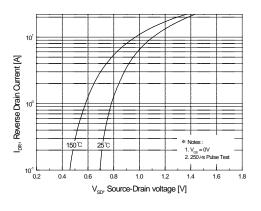


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

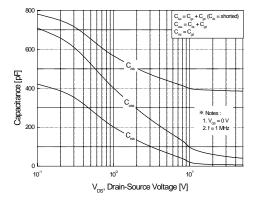


Figure 5. Capacitance Characteristics

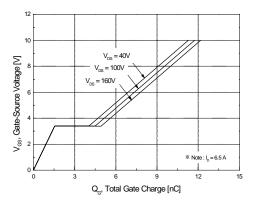
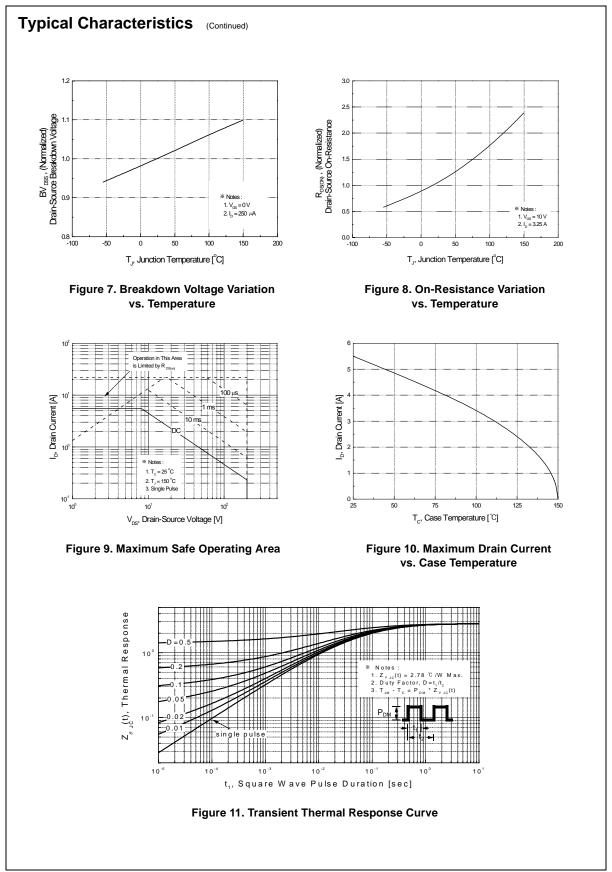


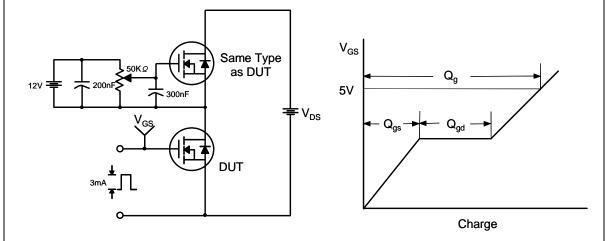
Figure 6. Gate Charge Characteristics

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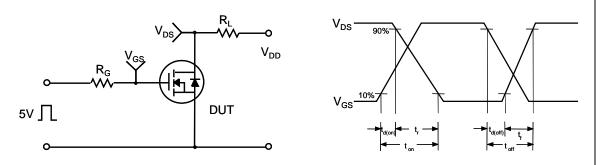


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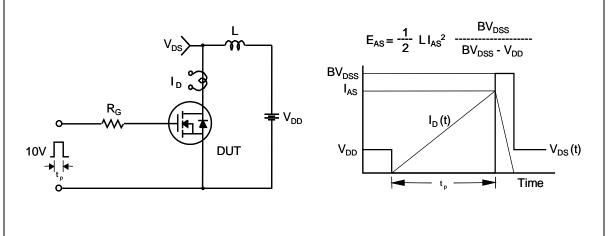
Gate Charge Test Circuit & Waveform



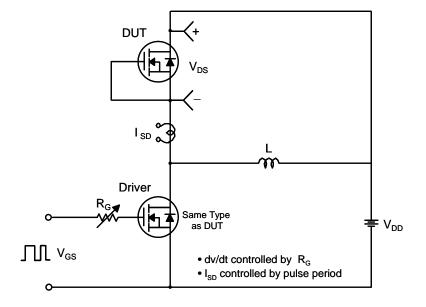
Resistive Switching Test Circuit & Waveforms

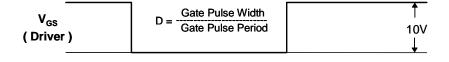


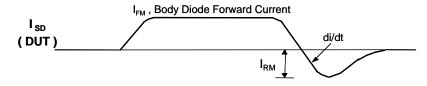
Unclamped Inductive Switching Test Circuit & Waveforms

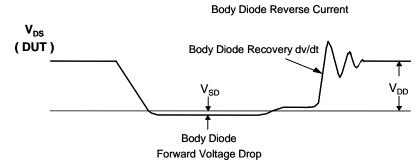


Peak Diode Recovery dv/dt Test Circuit & Waveforms



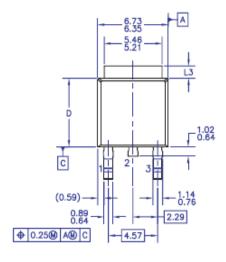


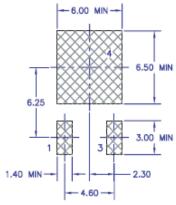


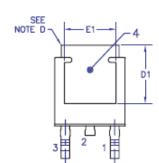


Mechanical Dimensions

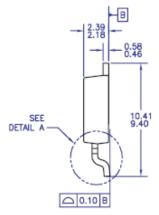
D - PAK

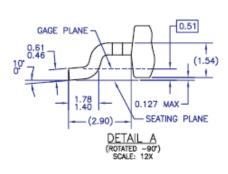




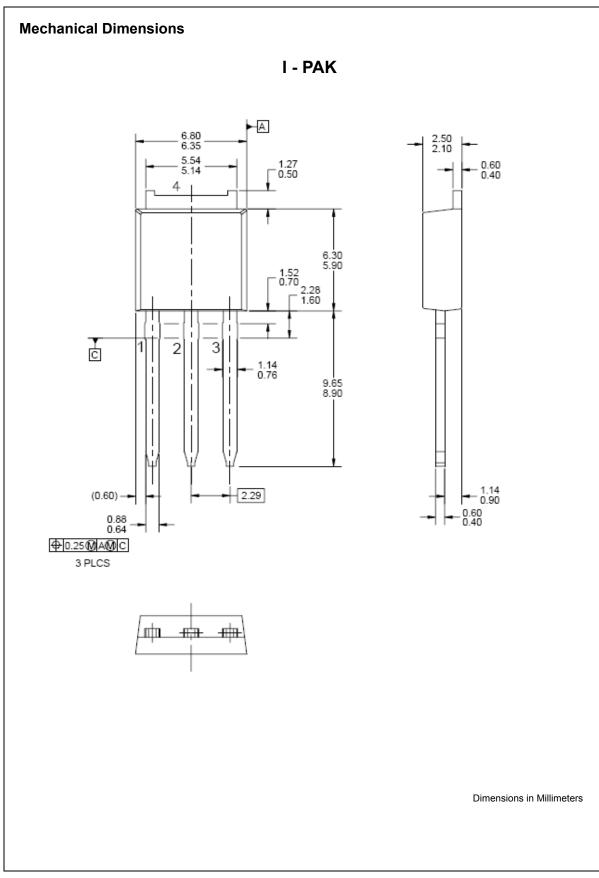








Dimensions in Millimeters



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